TOSHIBA Bi-CMOS Digital Integrated Circuit Silicon Monolithic

# **TB2901HQ**

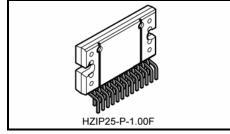
#### Maximum Power 47 W BTL x 4-ch Audio Power IC

The TB2901HQ is 4-ch BTL audio amplifier for car audio applications.

This IC can generate higher power:  $P_{OUT}$  MAX = 47 W as it includes the pure complementary P-ch and N-ch DMOS output stage.

It is designed to yield low distortion ratio for 4-ch BTL audio power amplifier, built-in standby function, muting function, and various kinds of protectors.

Additionally, high-side switch is built in.



Weight: 7.7 g (typ.)

#### **Features**

- High power output
  - : POUT MAX (1) = 47 W (typ.)

 $(V_{CC} = 14.4 \text{ V}, f = 1 \text{ kHz}, \text{JEITA max}, R_L = 4 \Omega)$ 

: POUT MAX (2) = 43 W (typ.)

 $(V_{CC} = 13.7 \text{ V}, f = 1 \text{ kHz}, \text{JEITA max}, R_L = 4 \Omega)$ 

POUT MAX (3) = 80 W (typ.)

 $(V_{CC} = 14.4 \text{ V}, f = 1 \text{ kHz}, \text{JEITA max}, R_L = 2 \Omega)$ 

: POUT(1) = 29 W (typ.)

 $(V_{CC} = 14.4 \text{ V}, f = 1 \text{ kHz}, THD = 10\%, RL = 4 \Omega)$ 

:  $P_{OUT}(2) = 25 \text{ W (typ.)}$ 

 $(\mathrm{V_{CC}}=13.2~\mathrm{V},\,\mathrm{f}=1~\mathrm{kHz},\,\mathrm{THD}=10\%,\,\mathrm{R_{L}}=4~\Omega)$ 

• Low distortion ratio: THD = 0.015% (typ.)

$$(V_{CC} = 13.2 \text{ V}, f = 1 \text{ kHz}, P_{OUT} = 5 \text{ W}, R_L = 4 \Omega)$$

• Low noise:  $V_{NO} = 90 \,\mu V_{rms}$  (typ.)

$$(V_{CC} = 13.2 \text{ V}, R_g = 0 \Omega, BW = 20 \text{ Hz} \sim 20 \text{ kHz}, R_L = 4 \Omega)$$

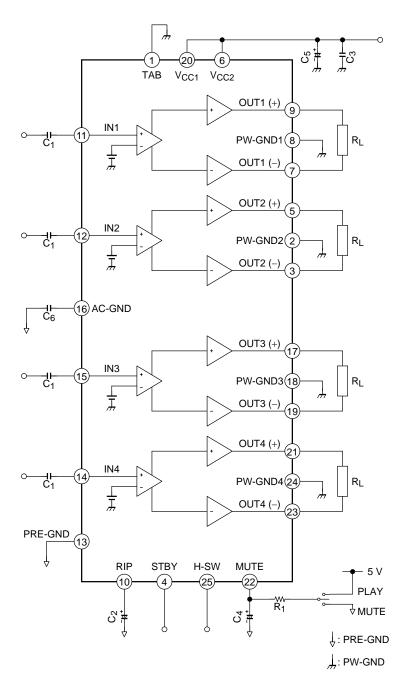
- Built-in standby switch function (pin 4)
- Built-in muting function (pin 22)
- Built-in high-side switch function (pin 25)
- Built-in various protection circuits:

Thermal shut down, overvoltage, out to GND, out to VCC, out to out short

- Operating supply voltage:  $V_{CC (opr)} = 9 \sim 18 \text{ V } (R_L = 4 \Omega)$ 
  - Note 1: Since this device's pins have a low withstanding voltage, please handle it with care.
  - Note 2: Install the product correctly. Otherwise, it may result in break down, damage and/or degradation to the product or equipment.
  - Note 3: These protection functions are intended to avoid some output short circuits or other abnormal conditions temporarily. These protect functions do not warrant to prevent the IC from being damaged.

    In case of the product would be operated with exceeded guaranteed operating ranges, these protection features may not operate and some output short circuits may result in the IC being damaged.
  - Note 4: The protection circuit may operate not correctly in case of the use of large phase-shift type speaker. Therefore, it should be confirmed that there is no problem on actual evaluation or mass-production board. Especially, it is necessary to be ware such a behavior when the large phase-shift type 20hm load, which is a kind of sub-woofer for example, is connected to this IC, though such kind of speaker use is not recommended.

## **Block Diagram**



Note5: Some of the functional blocks, circuits, or constants in the block diagram may be omitted or simplified for explanatory purpose.

#### **Caution and Application Method**

(Description is made only on the single channel.)

#### 1. Voltage Gain Adjustment

This IC has no NF (negative feedback) Pins. Therefore, the voltage gain can not be adjusted, but it makes the device a space and total costs saver.

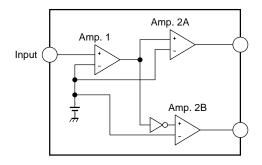


Figure 1 Block Diagram

$$\label{eq:continuous_section} \begin{split} The \ voltage \ gain \ of \ amp. 1 & : GV1 = 0dB \\ The \ voltage \ gain \ of \ amp. 2A, \ B & : GV2 = 20dB \\ The \ voltage \ gain \ of \ BTL \ connection: \ GV \ (BTL) = 6dB \end{split}$$

Therefore, the total voltage gain is decided by expression below.

$$G_V = G_{V1} + G_{V2} + G_{V}$$
 (BTL) =  $0 + 20 + 6 = 26dB$ 

#### 2. Standby SW Function (pin 4)

By means of controlling pin 4 (standby pin) to High and Low, the power supply can be set to ON and OFF. The threshold voltage of pin 4 is set at about 3VBE (typ.), and the power supply current is about 2  $\mu A$  (typ.) in the standby state.

#### Control Voltage of Pin 4: V<sub>SB</sub>

| Standby | Power | V <sub>SB</sub> (V) |
|---------|-------|---------------------|
| ON      | OFF   | 0~1.5               |
| OFF     | ON    | 3.5~6 V             |

When changing the time constant of pin 4, check the pop noise.

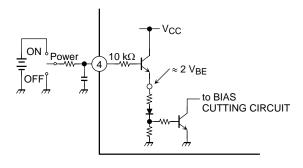


Figure 2 With pin 4 set to High, Power is turned ON

#### **Advantage of Standby SW**

- (1) Since VCC can directly be controlled to ON or OFF by the microcomputer, the switching relay can be omitted
- (2) Since the control current is microscopic, the switching relay of small current capacity is satisfactory for switching.

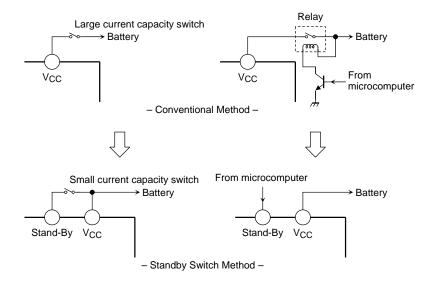


Figure 3

#### 3. Muting Function (pin 22)

Audio muting function is enabled when pin 22 is Low. When the time constant of the muting function is determined by  $R_1$  and  $C_4$ , it should take into account the pop noise. The pop noise which is generated when the power or muting function is turned ON/OFF will vary according to the time constant. (Refer to Figure 4 and Figure 5.)

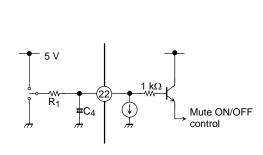
The pin 22 is designed to operate off 5 V.

Moreover, this terminal (pin 22) serves as the source switch of current of an internal mute circuit. And it is designed so that the discharge current of this terminal (pin 22) may serve as 200  $\mu$ A. The outside pull-up resistor  $R_1$  is determind on the basic of this value.

ex) When control voltage is changed in to 6 V from 5 V.

$$6~V/5~V\times47~k=56~k$$

To obtain enough mute attenuation, a series resistor,  $R_{1}$  at pin 22 should be 47  $k\Omega$  or more.



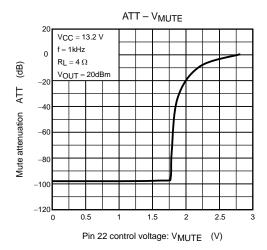


Figure 4 Muting Function

Figure 5 Mute Attenuation – V<sub>MUTE</sub> (V)

#### 4. High-Side Switch

Pin 25 of this device is used in concerned with  $V_{\rm CC}$  as a high-side switch which operates with the standby pin. Thus, both the power amp IC and the connected external unit (the hideaway unit) can be turned ON/OFF by using of the standby switch.

#### 5. Pop Noise Suppression

Since the AC-GND pin (pin 16) is used as the NF pin for all amps, the ratio between the input capacitance (C1) and the AC-to-GND capacitance (C6) should be 1:4.

Also, if the power is turned OFF before the C1 and C6 batteries have been completely charged, pop noise will be generated because of the DC input umbalance.

To counteract the noise, it is recommended that a longer charging time be used for C2 as well as for C1 and C6. Note that the time which audio output takes to start will be longer, since the C2 makes the muting time (the time from when the power is turned ON to when audio output starts) is fix.

The pop noise which is generated when the muting function is turned ON/OFF will vary according to the time constant of C4.

The greater the capacitance, the lower the pop noise. Note that the time from when the mute control signal is applied to C4 to when the muting function is turned ON/OFF will be longer.

#### 6. External Component Constants

| Component  | Recommended   |  | Eff  |                               |   |
|------------|---|--|--|-------------------------------|---|
| Name Value |   | Purpose                                  | Lower than recommended value                             | Higher than recommended value | Notes   |
| C1         | 0.22 μF   | To eliminate DC                          | Cut-off frequency is increased                           | Cut-off frequency is reduced  | Pop noise is generated when V <sub>CC</sub> is ON |
| C2         | 10 μF   | To reduce ripple                         | Powering ON/OFF is faster                                | Powering ON/OFF takes longer  |   |
| C3         | 0.1 μF  | To provide sufficient oscillation margin | Reduces noise and provides sufficient oscillation margin |                               |   |
| C4         | To reduce pop noise Duration until muting function is turned ON/OFF is short Low pop noise. Duration until muting function is turned ON/OFF is long |  |  |                               |   |
| C5         | 3900 μF   | Ripple filter                            | Power supply ripple filtering                            |                               |   |
| C6         | 1 μF  | NF for all outputs                       | Pop noise is suppressed when C1:C6 = 1:4                 |                               | Pop noise is generated when V <sub>CC</sub> is ON |

Note6: If recommended value is not used.

#### **Maximum Ratings (Ta = 25°C)**

| Characteristics             | Symbol                  | Rating  | Unit |
|-----------------------------|-------------------------|---------|------|
| Peak supply voltage (0.2 s) | V <sub>CC</sub> (surge) | 50      | V    |
| DC supply voltage           | V <sub>CC</sub> (DC)    | 25      | V    |
| Operation supply voltage    | V <sub>CC</sub> (opr)   | 18      | V    |
| Output current (peak) RL=4Ω | I <sub>O (peak)</sub>   | 9       | Α    |
| Output current (peak) RL=2Ω | I <sub>O (peak)-2</sub> | 6.3     | A    |
| Power dissipation           | P <sub>D</sub> (Note 6) | 125     | W    |
| Operation temperature       | T <sub>opr</sub>        | -40~85  | °C   |
| Storage temperature         | T <sub>stg</sub>        | -55~150 | °C   |

Note 7: Package thermal resistance  $\theta_{j-T} = 1^{\circ}\text{C/W}$  (typ.) (Ta = 25°C, with infinite heat sink)

The absolute maximum ratings of a semiconductor device are a set of specified parameter values, which must not be exceeded during operation, even for an instant. If any of these rating would be exceeded during operation, the device electrical characteristics may be irreparably altered and the reliability and lifetime of the device can no longer be guaranteed. Moreover, these operations with exceeded ratings may cause break down, damage and/or degradation to any other equipment. Applications using the device should be designed such that each maximum rating will never be exceeded in any operating conditions. Before using, creating and/or producing designs, refer to and comply with the precautions and conditions set forth in this documents.



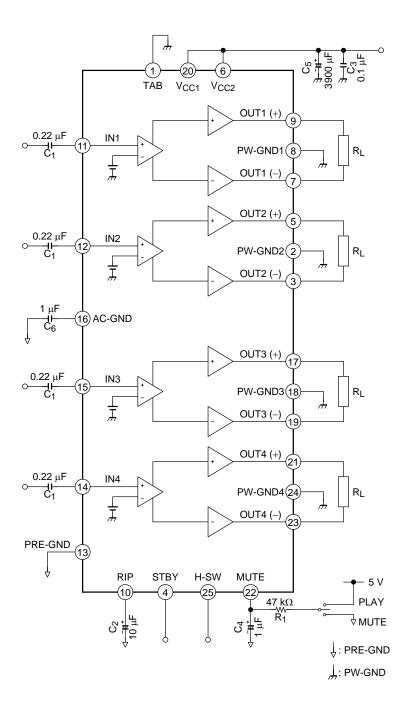
# Electrical Characteristics (unless otherwise specified, $V_{CC}$ = 13.2 V, f = 1 kHz, $R_L$ = 4 $\Omega$ , Ta = 25°C)

| Characteristics           | Symbol                   | Test<br>Circuit | Test Condition   | Min  | Тур.  | Max  | Unit  |  |
|---------------------------|--------------------------|-----------------|--|------|-------|------|-------|--|
| Quiescent current         | Iccq                     | _               | $V_{IN} = 0$   | _    | 200   | 400  | mA    |  |
|                           | P <sub>OUT</sub> MAX (1) | _               | V <sub>CC</sub> = 14.4 V, max POWER  | _    | 47    | _    |       |  |
|                           | P <sub>OUT</sub> MAX (2) | _               | V <sub>CC</sub> = 13.7 V, max POWER  | _    | 43    | _    |       |  |
| Output power              | P <sub>OUT</sub> MAX (3) | _               | $V_{CC}$ = 14.4 V, RL =2 $\Omega$ max POWER  |      | 80    |      |       |  |
|                           | P <sub>OUT</sub> (1)     | _               | V <sub>CC</sub> = 14.4 V, THD = 10%  |      | 29    |      |       |  |
|                           | P <sub>OUT</sub> (2)     | _               | THD = 10%  | 23   | 25    |      |       |  |
| Total harmonic distortion | THD                      | _               | P <sub>OUT</sub> = 5 W   |      | 0.015 | 0.15 | %     |  |
| Voltage gain              | G <sub>V</sub>           | _               | V <sub>OUT</sub> = 0.775 Vrms  | 24   | 26    | 28   | dB    |  |
| Voltage gain ratio        | ΔG <sub>V</sub>          | _               | V <sub>OUT</sub> = 0.775 Vrms  | -1.0 | 0     | 1.0  | dB    |  |
| Output noise voltage      | V <sub>NO</sub> (1)      | _               | Rg = 0 Ω, DIN45405   | _    | 100   | _    | μVrms |  |
|                           | V <sub>NO</sub> (2)      | _               | Rg = 0 Ω, BW = 20 Hz~20 kHz  | _    | 90    | 200  |       |  |
| Ripple rejection ratio    | R.R.                     | _               | $\begin{aligned} f_{rip} &= 100 \text{ Hz},  R_g = 620  \Omega \\ V_{rip} &= 0.775  \text{Vrms} \end{aligned}$ | 50   | 60    |      | dB    |  |
| Cross talk                | C.T.                     | _               | $\begin{array}{l} R_g = 620~\Omega \\ V_{OUT} = 0.775~Vrms \end{array}$  |      | 70    |      | dB    |  |
| Output offset voltage     | Voffset                  | _               |  | -150 | 0     | 150  | mV    |  |
| Input resistance          | R <sub>IN</sub>          | _               | _  | _    | 90    | _    | kΩ    |  |
| Standby current           | I <sub>SB</sub>          | _               | Standby condition  | _    | 2     | 10   | μА    |  |
| Standby control voltage   | V <sub>SB</sub> H        | _               | POWER: ON  | 3.5  | _     | 6.0  | V     |  |
|                           | V <sub>SB</sub> L        | _               | POWER: OFF   | 0    | _     | 1.5  | V     |  |
| Mute control voltage      | V <sub>M</sub> H         | _               | MUTE: OFF  | 3.0  | _     | 6.0  | V     |  |
|                           | V <sub>M</sub> L         | _               | MUTE: ON, $R_1 = 47 \text{ k}\Omega$   | 0    | _     | 0.5  | V     |  |
| Mute attenuation          | ATT M                    | _               | MUTE: ON<br>V <sub>OUT</sub> = 7.75 Vrms→Mute: OFF   | 80   | 90    |      | dB    |  |

# **High-Side Switch**

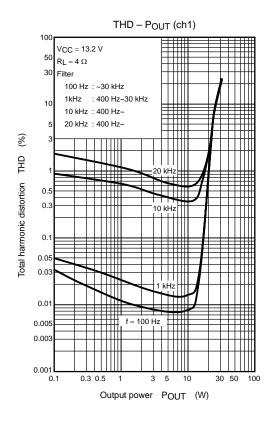
| Output current  | IO              | _ |                                     | 400 |      |     | mA |
|---|-----------------|---|-------------------------------------|-----|------|-----|----|
| Difference voltage between V <sub>CC</sub> and output | ΔV <sub>o</sub> | _ | I <sub>O</sub> = 400 mA, +B = 9.6 V | _   | 0.25 | 0.6 | V  |

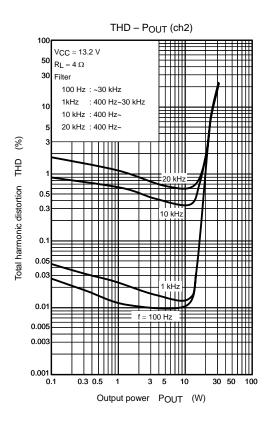
#### **Test Circuit**

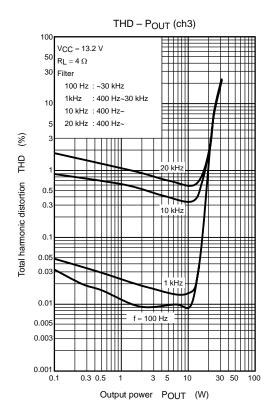


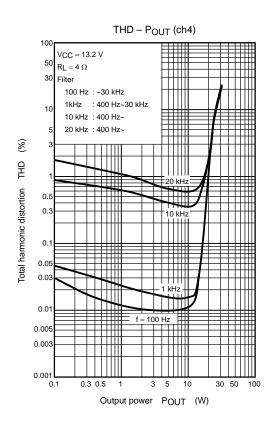
Components in the test circuits are only used to obtain and confirm the device characteristics.

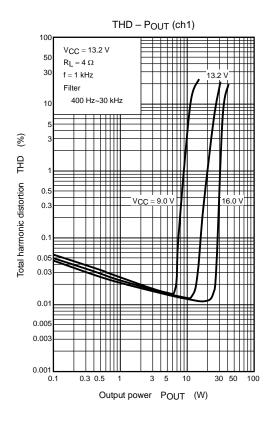
These components and circuits do not warrant to prevent the application equipment from malfunction or failure.

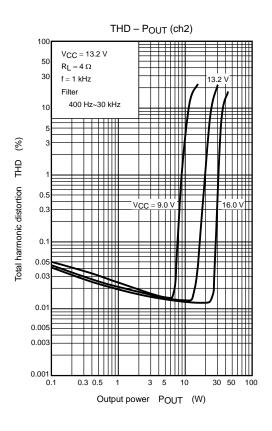


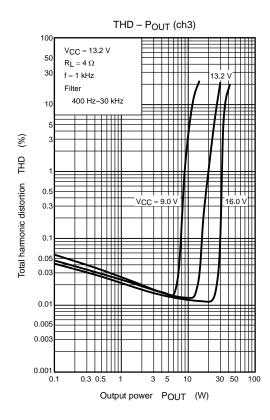


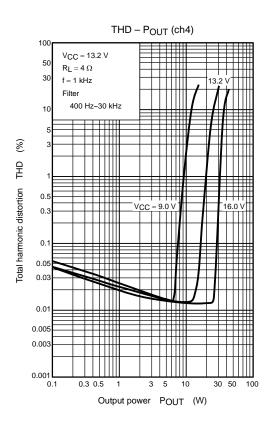


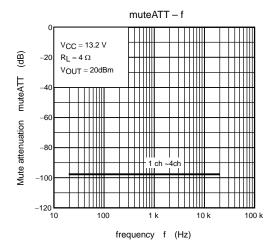


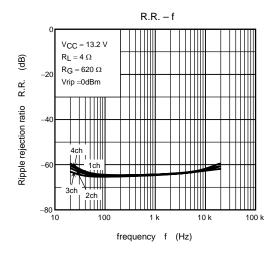


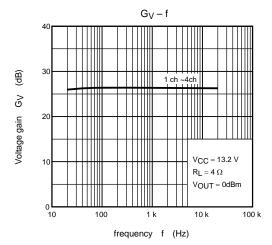


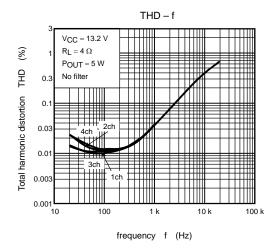


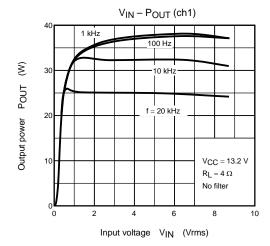


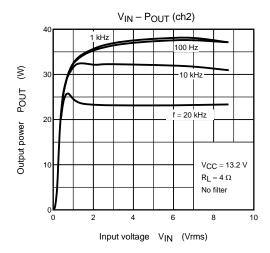


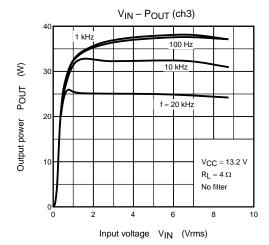


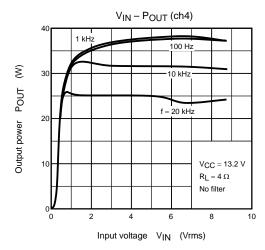


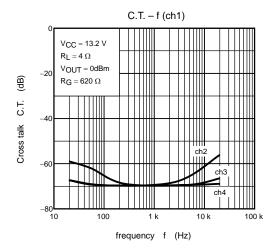


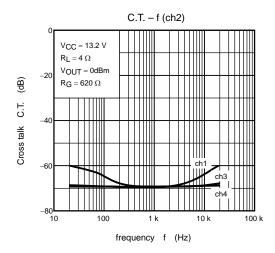


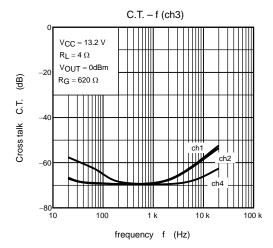


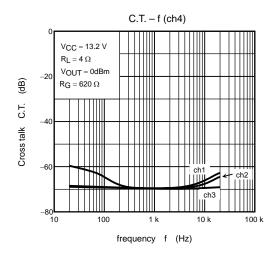


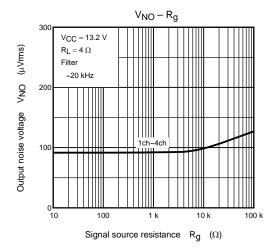


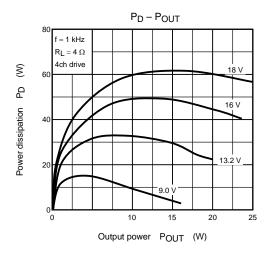


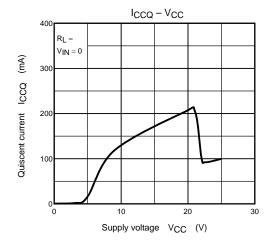


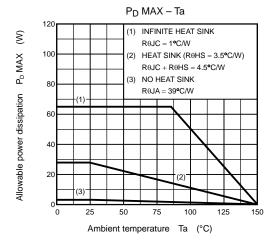






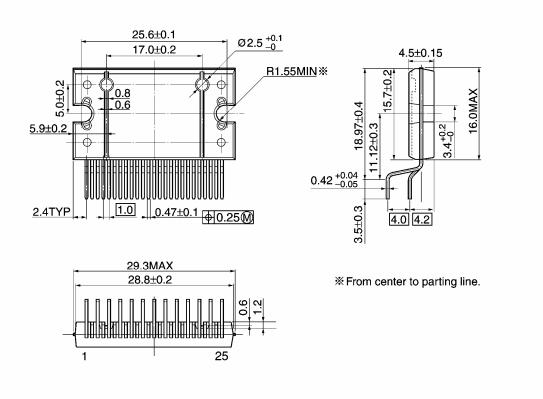






## **Package Dimensions**

HZIP25-P-1.00F Unit: mm



Weight: 7.7 g (typ.)

About solderability, following conditions were confirmed

- Solderability
  - (1) Use of Sn-63Pb solder Bath
    - solder bath temperature = 230°C
    - · dipping time = 5 seconds
    - · the number of times = once
    - · use of R-type flux
  - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
    - solder bath temperature = 245°C
    - · dipping time = 5 seconds
    - · the number of times = once
    - · use of R-type flux

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